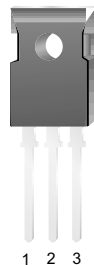


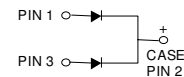
# MBR3035PT - MBR3060PT

## Features

- Low power loss, high efficiency.
- High surge capacity.
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.
- Metal silicon junction, majority carrier conduction.
- High current capacity, low forward voltage drop.
- Guard ring for over voltage protection.



TO-3P/TO-247AD



## Schottky Rectifiers

### Absolute Maximum Ratings\*

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value				Units
		3035PT	3045PT	3050PT	3060PT	
$V_{RRM}$	Maximum Repetitive Reverse Voltage	35	45	50	60	V
$I_{F(AV)}$	Average Rectified Forward Current	30				A
$I_{FSM}$	Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave	200				A
$T_{stg}$	Storage Temperature Range	-65 to +175				$^\circ\text{C}$
$T_J$	Operating Junction Temperature	-65 to +150				$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## Thermal Characteristics

Symbol	Parameter	Value	Units
$P_D$	Power Dissipation	3.0	W
$R_{\theta JL}$	Thermal Resistance, Junction to Lead	1.4	$^\circ\text{C}/\text{W}$

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Device				Units
		3035PT	3045PT	3050PT	3060PT	
$V_F$	Forward Voltage $I_F = 20\text{ A}$ , $T_C = 25^\circ\text{C}$	-	-	0.75	0.75	V
	$I_F = 20\text{ A}$ , $T_C = 125^\circ\text{C}$	0.60	0.60	0.65	0.65	V
	$I_F = 30\text{ A}$ , $T_C = 25^\circ\text{C}$	0.76	0.76	-	-	V
	$I_F = 30\text{ A}$ , $T_C = 125^\circ\text{C}$	0.72	0.72	-	-	V
$I_R$	Reverse Current @ rated $V_R$ $T_A = 25^\circ\text{C}$	1.0	1.0	5.0	5.0	mA
	$T_A = 125^\circ\text{C}$	60	60	100	100	mA
$I_{RRM}$	Peak Repetitive Reverse Surge Current 2.0 $\mu\text{s}$ Pulsu Width, $f = 1.0\text{ KHz}$	1.0	1.0	0.5	0.5	A

# Schottky Rectifier

(continued)

## Typical Characteristics

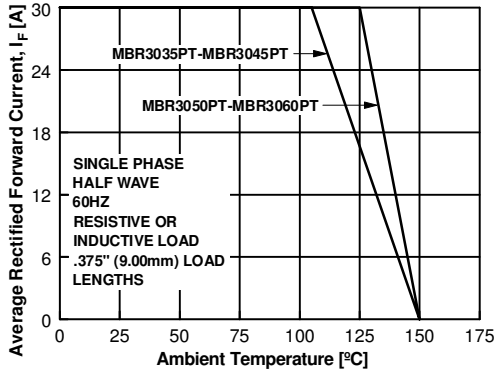


Figure 1. Forward Current Derating Curve

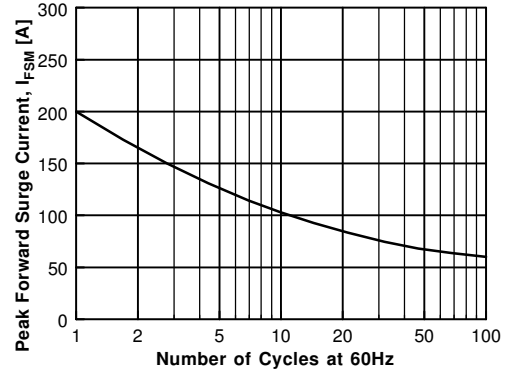


Figure 2. Non-Repetitive Surge Current

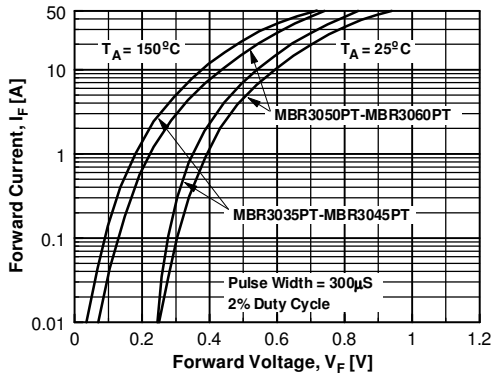


Figure 3. Forward Voltage Characteristics

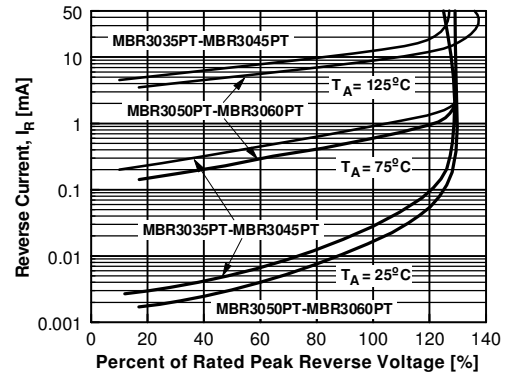


Figure 4. Reverse Current vs Reverse Voltage

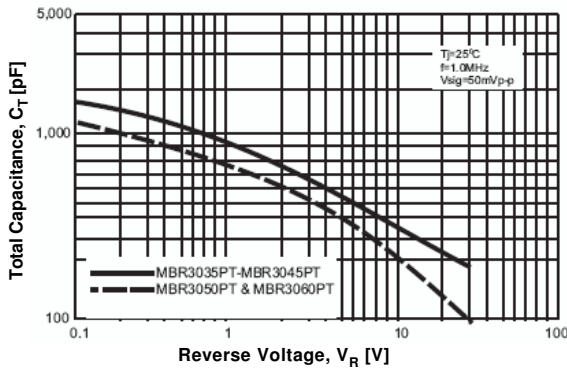


Figure 5. Total Capacitance

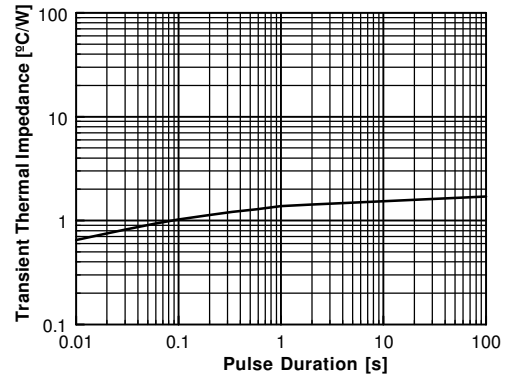


Figure 6. Thermal Impedance Characteristics

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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